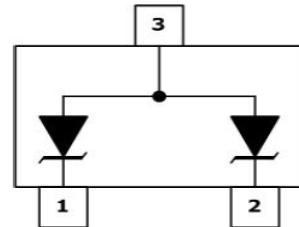


Features

- Unidirectional ESD protection of two lines
- Low diode capacitance: $C_d = 17 \text{ pF}$
- Max. peak pulse power: $P_{PP} = 160 \text{ W}$
- Low clamping voltage: $V_{CL} = 55 \text{ V}$
- Ultra low leakage current: $I_{RM} \leq 1 \mu\text{A}$
- ESD protection up to 30 kV
- IEC 61000-4-2; level 4 (ESD)
- IEC 61000-4-5 (surge); $I_{PP} = 2.5 \text{ A}$
- AEC-Q101 qualified



Applications

- Computers and peripherals
- Audio and video equipment
- Cellular handsets and accessories
- Subscriber Identity Module (SIM) card protection
- Portable electronics
- Communication systems
- 10/100 Mbit/s Ethernet

MACHANICAL DATA

- SOT-23 package
- Flammability Rating: UL 94V-0
- Packaging: Tape and Reel
- High temperature soldering guaranteed: 260°C/10S
- MSL 1

Quick reference data

$T_{amb} = 25 \text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per diode						
V_{RWM}	reverse standoff voltage		-	-	36	V
C_d	diode capacitance	$f = 1 \text{ MHz}; V_R = 0 \text{ V}$	-	17	35	pF

Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per diode						
I_{PP}	peak pulse power	$t_p = 8/20 \mu s$	[1][2]	-	160	W
I_{PP}	peak pulse current	$t_p = 8/20 \mu s$	[1][2]	-	2.5	A
Per device						
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			-55	+150	°C
T_{stg}	storage temperature			-65	+150	°C

[1] Non-repetitive current pulse 8/20 μs exponential decay waveform according to IEC 61000-4-5.

[2] Measured from pin 1 or 2 to pin 3.

ESD maximum ratings

$T_{amb} = 25$ °C unless otherwise specified.

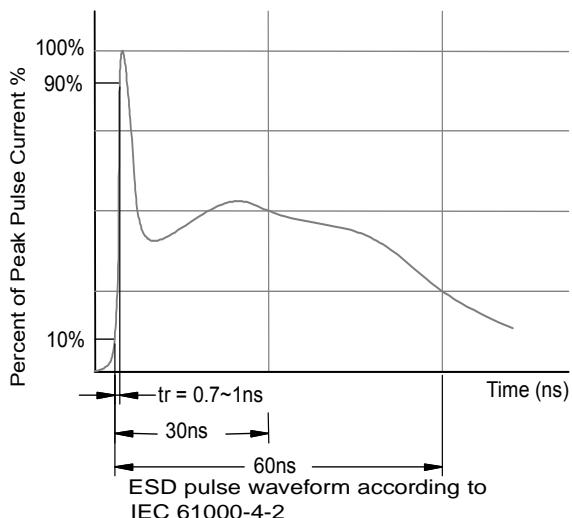
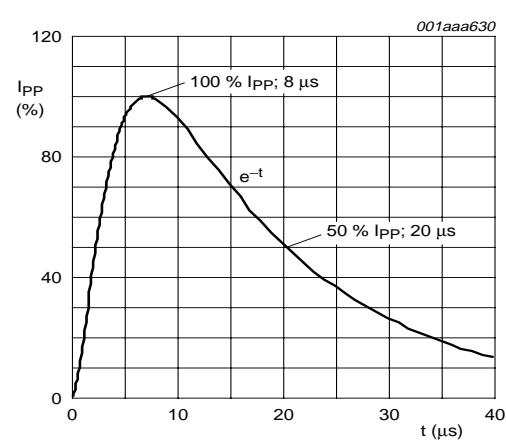
Symbol	Parameter	Conditions		Min	Max	Unit
Per diode						
V_{ESD}	electrostatic discharge voltage	IEC 61000-4-2 (contact discharge)	[1][2]	-	30	kV
		machine model	[2]	-	400	V
		MIL-STD-883 (human body model)		-	8	kV

[1] Device stressed with ten non-repetitive ESD pulses.

[2] Measured from pin 1 to pin 2.

ESD standards compliance

Standard	Conditions
Per diode	
IEC 61000-4-2; level 4 (ESD)	> 15 kV (air); > 8 kV (contact)
MIL-STD-883; class 3 (human body model)	> 4 kV



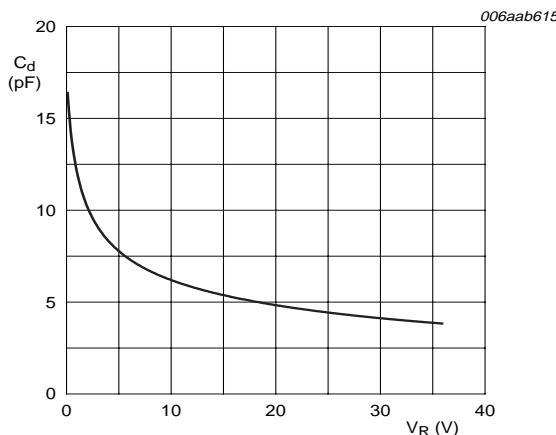
Characteristics

$T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per diode							
V_{RWM}	reverse standoff voltage			-	-	36	V
I_{RM}	reverse leakage current	$V_{RWM} = 30\text{ V}$		-	< 0.02	1	μA
V_{BR}	breakdown voltage	$I_R = 5\text{ mA}$		40	44	-	V
C_d	diode capacitance	$f = 1\text{ MHz}; V_R = 0\text{ V}$	[1]	-	17	35	pF
V_{CL}	clamping voltage	$I_{PP} = 1\text{ A}$	[1][2]	-	55	60	V
r_{dif}	differential resistance	$I_R = 0.5\text{ mA}$		-	-	300	Ω

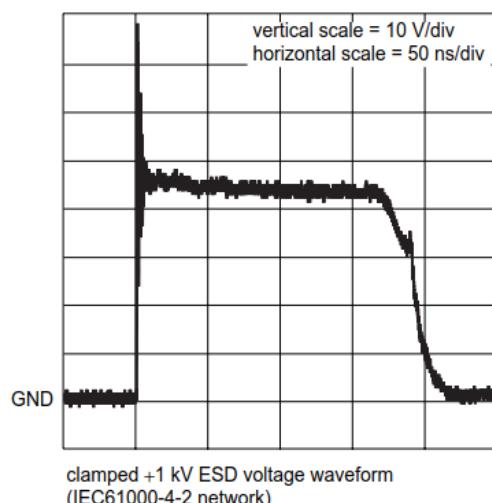
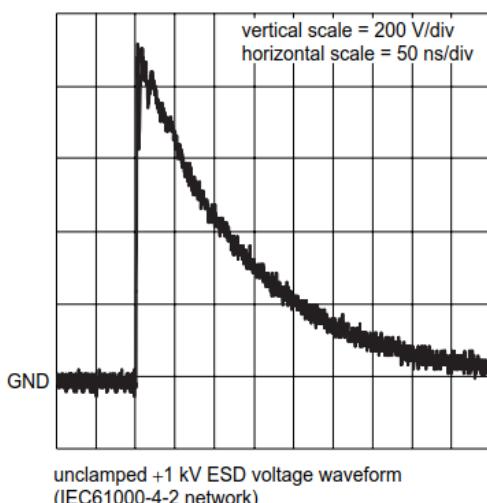
[1] Measured from pin 1 or 2 to pin 3.

[2] Non-repetitive current pulse 8/20 μs exponential decay waveform according to IEC 61000-4-5.

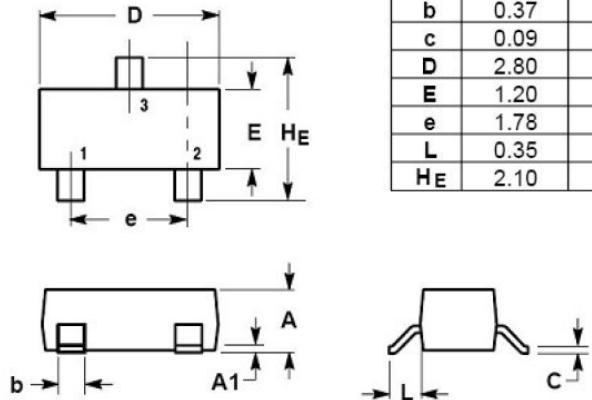


$f = 1\text{ MHz}; T_{amb} = 25^{\circ}\text{C}$

Diode capacitance as a function of reverse voltage; typical values

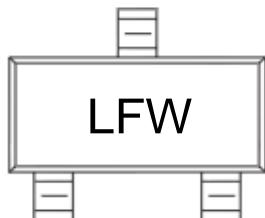


SOT-23 PACKAGE OUTLINE DIMENSIONS



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.40	2.64	0.083	0.094	0.104

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW PESD36VS2UT	SOT-23	3000	Tape and reel

单击下面可查看定价，库存，交付和生命周期等信息

[>>UMW\(友台半导体\)](#)